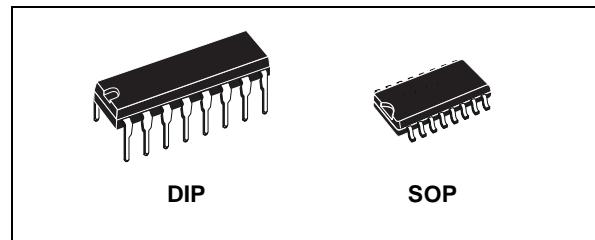




## QUAD NOR 3-STATE R-S LATCH

- QUIESCENT CURRENT SPECIFIED UP TO 20V
- 3-LEVEL OUTPUTS WITH COMMON OUTPUT ENABLE
- SEPARATE SET AND RESET INPUT FOR EACH LATCH
- 5V, 10V AND 15V PARAMETRIC RATINGS
- INPUT LEAKAGE CURRENT  
 $I_I = 100\text{nA}$  (MAX) AT  $V_{DD} = 18\text{V}$   $T_A = 25^\circ\text{C}$
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC JESD13B " STANDARD SPECIFICATIONS FOR DESCRIPTION OF B SERIES CMOS DEVICES"



### ORDER CODES

PACKAGE	TUBE	T & R
DIP	HCF4043BEY	
SOP	HCF4043BM1	HCF4043M013TR

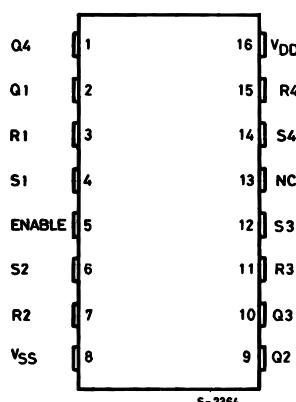
### DESCRIPTION

The HCF4043B is a monolithic integrated circuit fabricated in Metal Oxide Semiconductor technology available in DIP and SOP packages. The HCF4043B is a quad cross-coupled 3-state CMOS NOR latch.

Each latch has a separate Q output and individual SET and RESET input. The Q outputs are

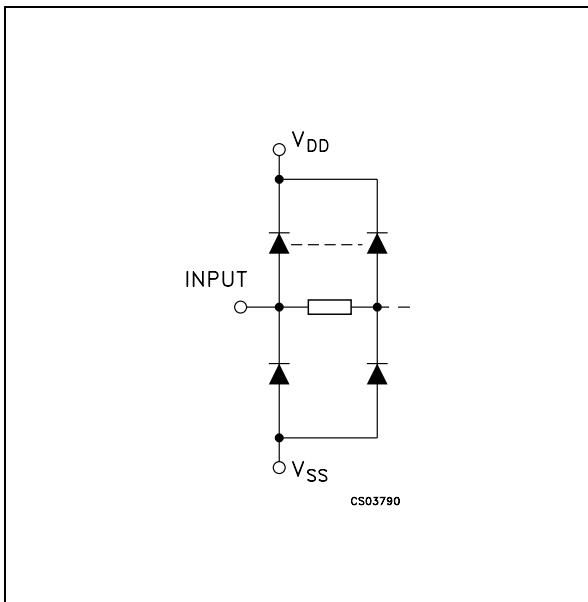
controlled by a common ENABLE input. A logic "1" or "high" on the ENABLE inputs connects the latch states to the Q outputs. A logic "0" or "low" on the ENABLE input disconnects the latch states from the Q outputs, resulting in an open circuit condition on the Q outputs. The open circuit feature allows common bussing of the outputs.

### PIN CONNECTION



# HCF4043B

## INPUT EQUIVALENT CIRCUIT



## PIN DESCRIPTION

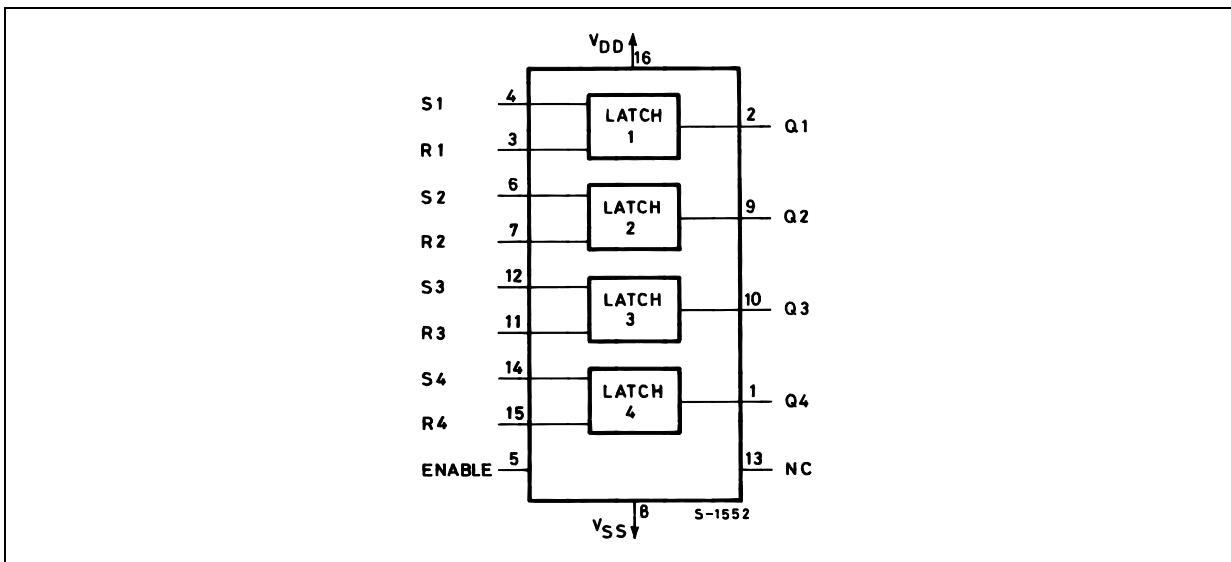
PIN No	SYMBOL	NAME AND FUNCTION
4, 6, 12, 14	S1 to S4	Set Inputs
3, 7, 11, 15	R1 to R4	Reset Inputs
5	ENABLE	Enable Input
2, 9, 10, 1	Q1 to Q4	Outputs
13	NC	Not Connected
8	V <sub>SS</sub>	Negative Supply Voltage
16	V <sub>DD</sub>	Positive Supply Voltage

## TRUTH TABLE

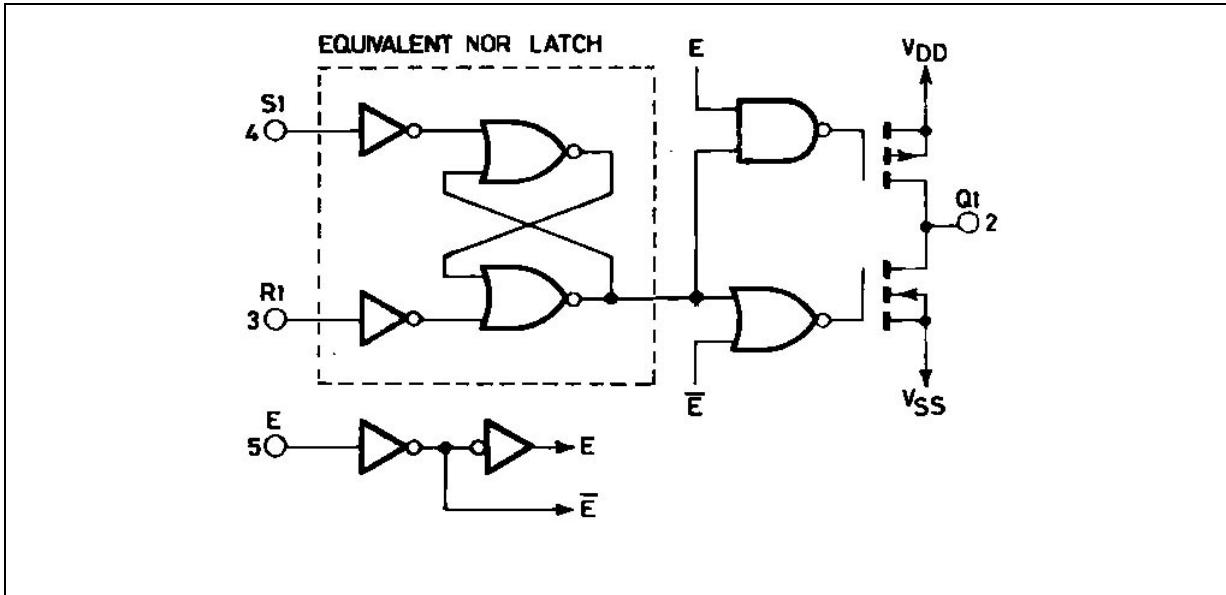
INPUTS			OUTPUT Q <sub>n</sub>
ENABLE	S <sub>n</sub>	R <sub>n</sub>	
L	X	X	Z
H	L	H	L
H	H	X	H
H	L	L	LATCHED

X : Don't Care

## FUNCTIONAL DIAGRAM



## LOGIC DIAGRAM



## ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V <sub>DD</sub>	Supply Voltage	-0.5 to +22	V
V <sub>I</sub>	DC Input Voltage	-0.5 to V <sub>DD</sub> + 0.5	V
I <sub>I</sub>	DC Input Current	± 10	mA
P <sub>D</sub>	Power Dissipation per Package	200	mW
	Power Dissipation per Output Transistor	100	mW
T <sub>op</sub>	Operating Temperature	-55 to +125	°C
T <sub>stg</sub>	Storage Temperature	-65 to +150	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied.

All voltage values are referred to V<sub>SS</sub> pin voltage.

## RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V <sub>DD</sub>	Supply Voltage	3 to 20	V
V <sub>I</sub>	Input Voltage	0 to V <sub>DD</sub>	V
T <sub>op</sub>	Operating Temperature	-55 to 125	°C

**DC SPECIFICATIONS**

Symbol	Parameter	Test Condition				Value						Unit	
		V <sub>I</sub> (V)	V <sub>O</sub> (V)	I <sub>OL</sub>   (μA)	V <sub>DD</sub> (V)	T <sub>A</sub> = 25°C			-40 to 85°C		-55 to 125°C		
						Min.	Typ.	Max.	Min.	Max.	Min.	Max.	
I <sub>L</sub>	Quiescent Current	0/5			5		0.02	1		30		30	μA
		0/10			10		0.02	2		60		60	
		0/15			15		0.02	4		120		120	
		0/20			20		0.04	20		600		600	
V <sub>OH</sub>	High Level Output Voltage	0/5		<1	5	4.95			4.95		4.95		V
		0/10		<1	10	9.95			9.95		9.95		
		0/15		<1	15	14.95			14.95		14.95		
V <sub>OL</sub>	Low Level Output Voltage	5/0		<1	5		0.05			0.05		0.05	V
		10/0		<1	10		0.05			0.05		0.05	
		15/0		<1	15		0.05			0.05		0.05	
V <sub>IH</sub>	High Level Input Voltage		0.5/4.5	<1	5	3.5			3.5		3.5		V
			1/9	<1	10	7			7		7		
			1.5/13.5	<1	15	11			11		11		
V <sub>IL</sub>	Low Level Input Voltage		4.5/0.5	<1	5			1.5		1.5		1.5	V
			9/1	<1	10			3		3		3	
			13.5/1.5	<1	15			4		4		4	
I <sub>OH</sub>	Output Drive Current	0/5	2.5	<1	5	-1.36	-3.2		-1.15		-1.1		mA
		0/5	4.6	<1	5	-0.44	-1		-0.36		-0.36		
		0/10	9.5	<1	10	-1.1	-2.6		-0.9		-0.9		
		0/15	13.5	<1	15	-3.0	-6.8		-2.4		-2.4		
I <sub>OL</sub>	Output Sink Current	0/5	0.4	<1	5	0.44	1		0.36		0.36		mA
		0/10	0.5	<1	10	1.1	2.6		0.9		0.9		
		0/15	1.5	<1	15	3.0	6.8		2.4		2.4		
I <sub>I</sub>	Input Leakage Current	0/18	Any Input		18		±10 <sup>-5</sup>	±0.1		±1		±1	μA
I <sub>OZ</sub>	3-State Output	0/18	0/18		18		±10 <sup>-4</sup>	±0.4		±12		±12	μA
C <sub>I</sub>	Input Capacitance		Any Input				5	7.5					pF

The Noise Margin for both "1" and "0" level is: 1V min. with V<sub>DD</sub>=5V, 2V min. with V<sub>DD</sub>=10V, 2.5V min. with V<sub>DD</sub>=15V

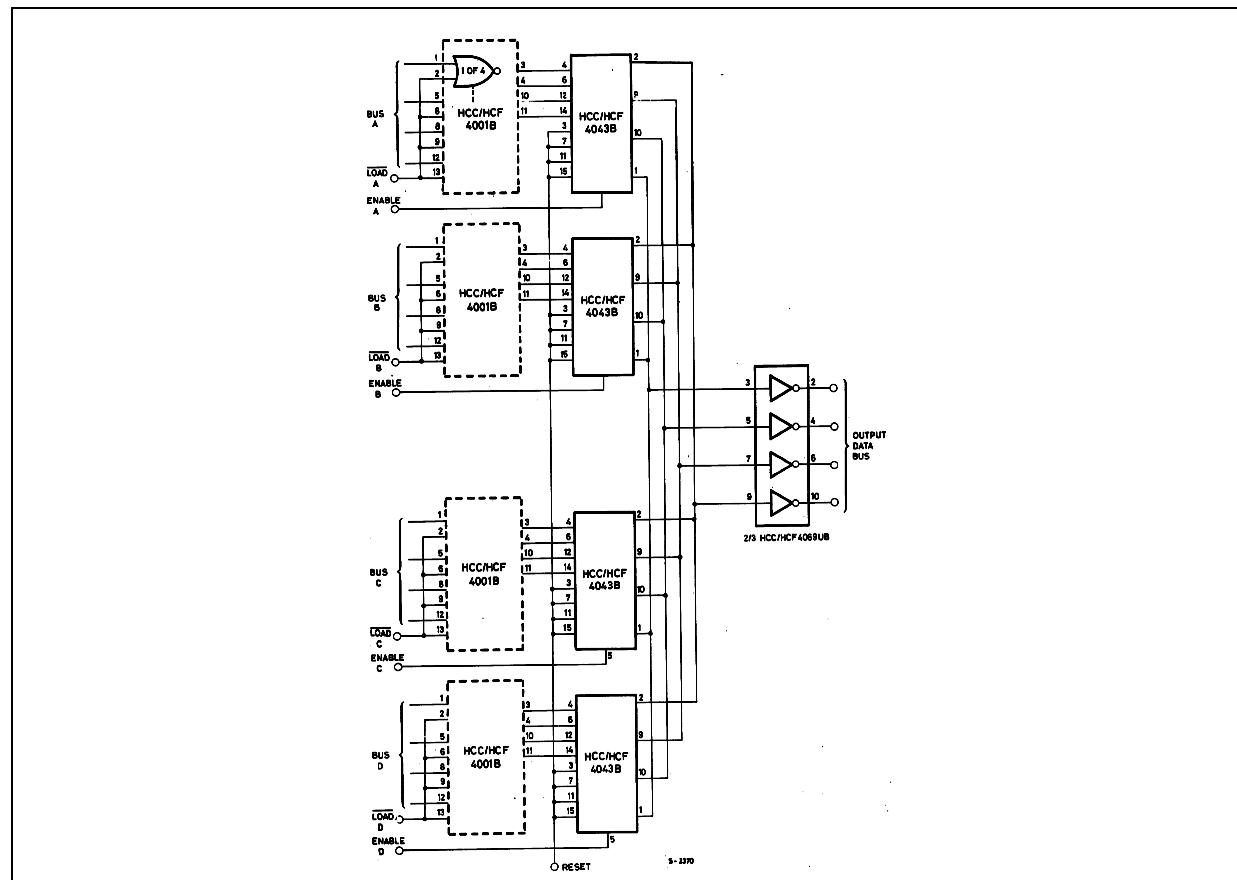
DYNAMIC ELECTRICAL CHARACTERISTICS ( $T_{amb} = 25^\circ C$ ,  $C_L = 50\text{pF}$ ,  $R_L = 200K\Omega$ ,  $t_r = t_f = 20\text{ ns}$ )

Symbol	Parameter	Test Condition		Value (*)			Unit
		$V_{DD}$ (V)		Min.	Typ.	Max.	
$t_{PLH}$ $t_{PHL}$	Propagation Delay Time (SET or RESET to Q)	5			150	300	ns
		10			70	140	
		15			50	100	
$t_{PZH}$ $t_{PZL}$	3-State Propagation Delay Time (Enable to Q)	5			115	230	ns
		10			55	110	
		15			40	80	
$t_{PLZ}$ $t_{PHZ}$	3-State Propagation Delay Time (Disable to Q)	5			90	180	ns
		10			50	100	
		15			35	70	
$t_{TLH}$ $t_{THL}$	Transition Time	5			100	200	ns
		10			50	100	
		15			40	80	
$t_W$	Pulse Width (Set or Reset)	5			160	80	ns
		10			80	40	
		15			40	20	

(\*) Typical temperature coefficient for all  $V_{DD}$  value is 0.3 %/ $^\circ C$ .

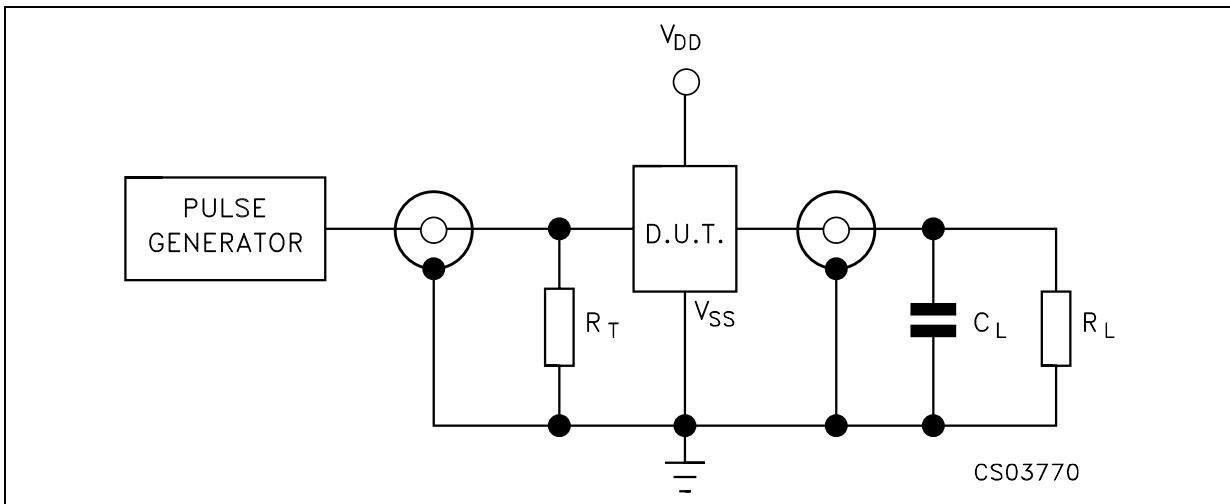
## TYPICAL APPLICATIONS

## MULTIPLE BUS STORAGE



# HCF4043B

## TEST CIRCUIT

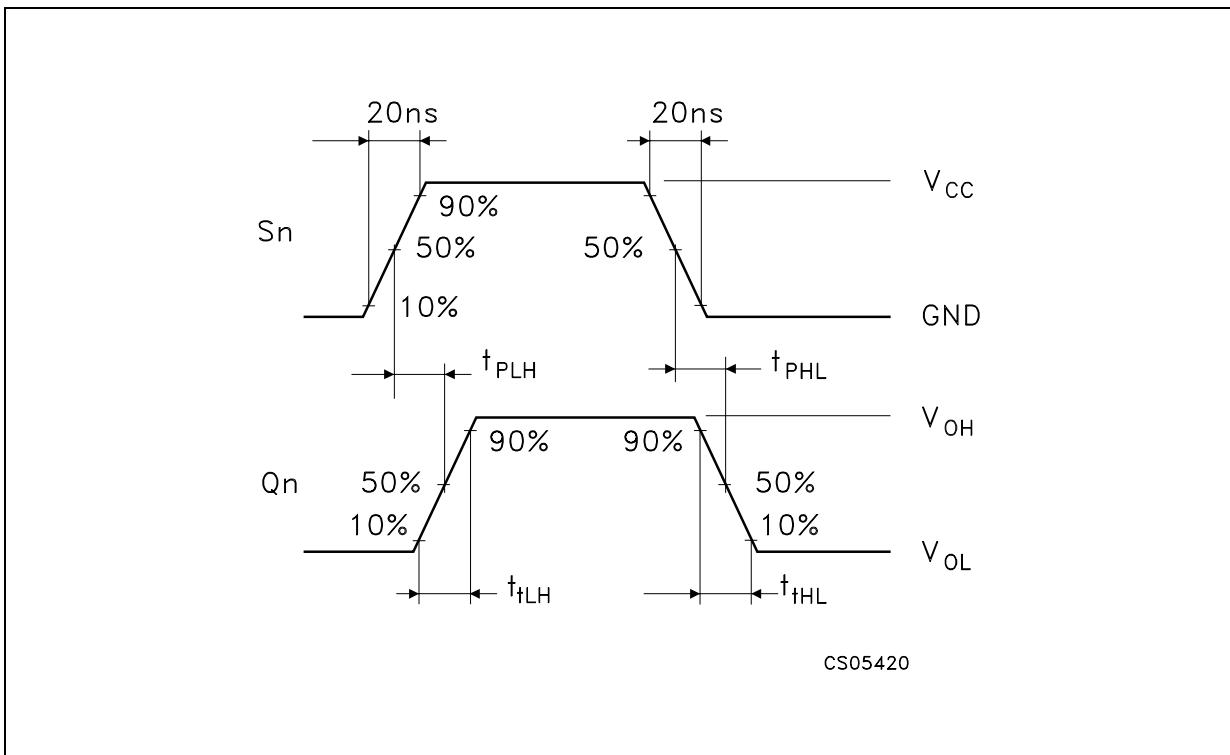


$C_L = 50\text{pF}$  or equivalent (includes jig and probe capacitance)

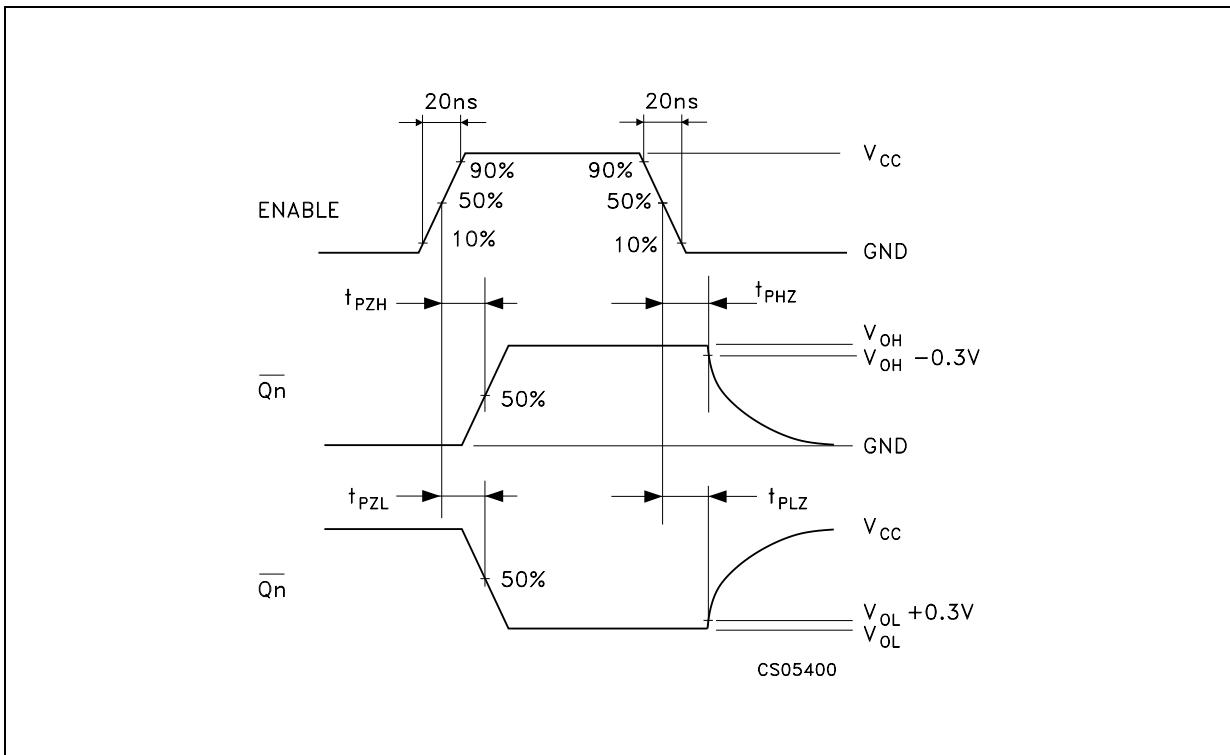
$R_L = 200\text{K}\Omega$

$R_T = Z_{\text{OUT}}$  of pulse generator (typically  $50\Omega$ )

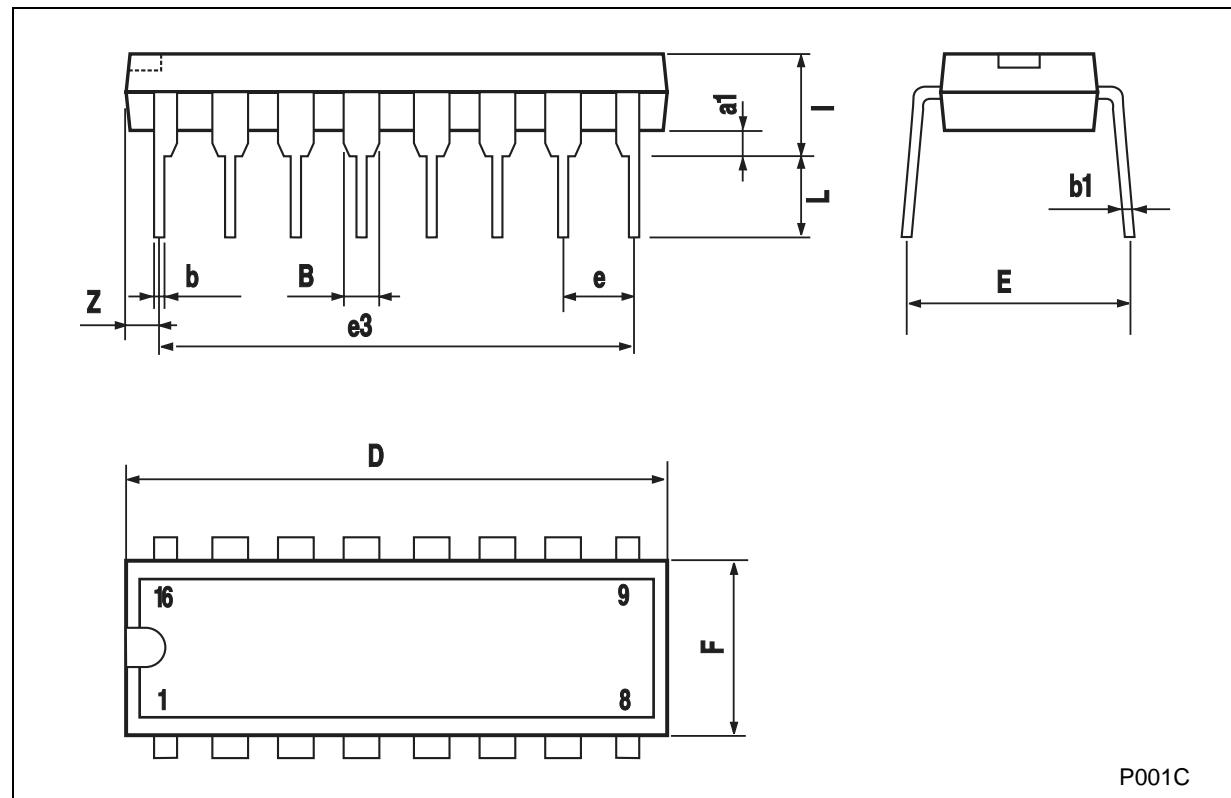
## WAVEFORM : PROPAGATION DELAY TIMES (f=1MHz; 50% duty cycle)



## WAVEFORM 2 : OUTPUT ENABLE AND DISABLE TIMES (f=1MHz; 50% duty cycle)



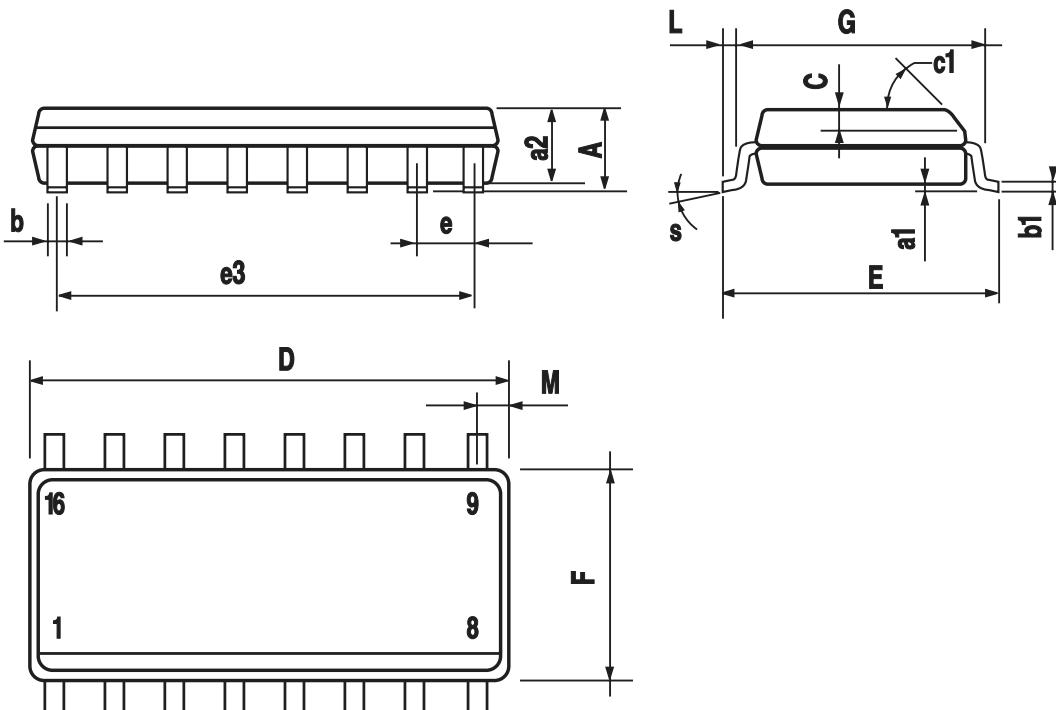
Plastic DIP-16 (0.25) MECHANICAL DATA						
DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
a1	0.51			0.020		
B	0.77		1.65	0.030		0.065
b		0.5			0.020	
b1		0.25			0.010	
D			20			0.787
E		8.5			0.335	
e		2.54			0.100	
e3		17.78			0.700	
F			7.1			0.280
I			5.1			0.201
L		3.3			0.130	
Z			1.27			0.050



P001C

## SO-16 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.75			0.068
a1	0.1		0.2	0.003		0.007
a2			1.65			0.064
b	0.35		0.46	0.013		0.018
b1	0.19		0.25	0.007		0.010
C		0.5			0.019	
c1	45° (typ.)					
D	9.8		10	0.385		0.393
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		8.89			0.350	
F	3.8		4.0	0.149		0.157
G	4.6		5.3	0.181		0.208
L	0.5		1.27	0.019		0.050
M			0.62			0.024
S	8° (max.)					



PO13H

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